

IN THE CLAIMS

Please amend the claims in accordance with the following rewritten claims in clean form. Applicant includes herewith an Attachment for Claim Amendments showing a marked up version of each amended claim.

*Claim 3*  
3. (Amended) A semiconductor device according to claim 1 characterized in operating in a fully depleted operation mode.

*Claim 4*  
4. (Amended) A semiconductor device according to claim 1, wherein the SOI substrate is a substrate composed of a glass substrate, a quartz substrate or another insulation substrate and a semiconductor film formed thereon.

*Claim 8*  
8. (Amended) A method for manufacturing a semiconductor device according claim 5, wherein the junction depth of the extension regions is formed to be 50% or less of the junction depth of each of the source region and the drain region.